

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet 1

of

2

Complete if Known

Application Number

Filing Date

December 1, 2003

First Named Inventor

Crocifisso Marco Antonio Renna

Art Unit

Examiner Name

Attorney Docket Number

2110-91-3

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
MNT		US-2002/076896 A1	06/20/02	Farrar, et al.	
		US-2002/070419 A1	06/13/02	Farrar, et al.	
		US-5,324,683	06/28/94	Fitch, et al.	
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FOREIGN PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				
MNT		DE 1001 31 249 A	05/23/02	Wacker Siltronic Halbleiternat		
		EP 1 073 112 A	01/31/01	STMicroelectron ics, S.r.l.		
		EP 1 113 492 A	07/04/01	STMicroelectron ics, S.r.l.		

Examiner
Signature

Mance D. Homan

Date
Considered

10/13/05

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Sheet 2 of 2

Complete if Known

Application Number	
Filing Date	December 1, 2003
First Named Inventor	Crocifisso Marco Antonio Renna
Group Art Unit	
Examiner Name	
Attorney Docket Number	2110-91-3

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MDH		European Search Report for 02425742.0 dated August 6, 2003	
		Tsunashima, et al. "A New Substrate Engineering Technique to Realize Silicon on Nothing" Electrochemical Society Proceedings, Electrochemical Society, Pennington, NJ, US, No. 17, 2000, pp. 532-545, XP008004134 ISSN: 0161-8374	
↓		Sato, et al. "SON (silicon on nothing) MOSFET Using ESS (empty space in silicon) Technique for SoC Applications" International Electron Devices Meeting 2001. IEDM. Technical Digest. Washington, DC, Dec. 2-5, 2001, New York, NY: IEEE, U.S., 2 December 2001, pp. 3771-3774, XP010575245 ISBN: 0-7803-7050-3	

Examiner Signature	<i>Monica D. Plamen</i>	Date Considered	10/13/05
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